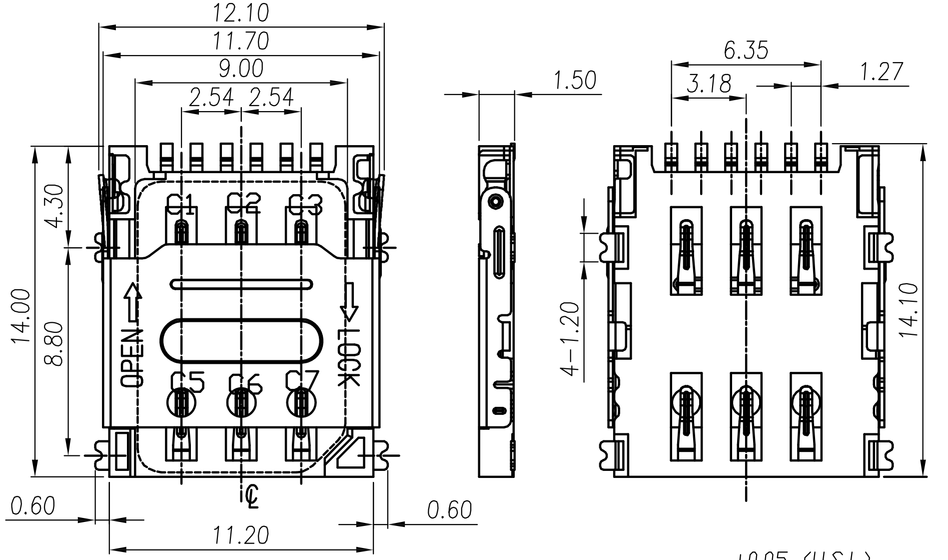
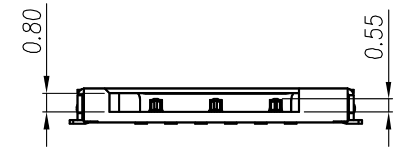
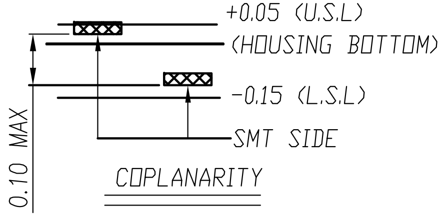
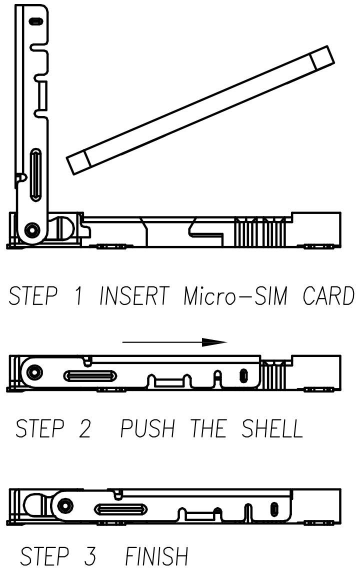
REV.	ECN.NO.	APPD.
A	/	/







COPLANARITY



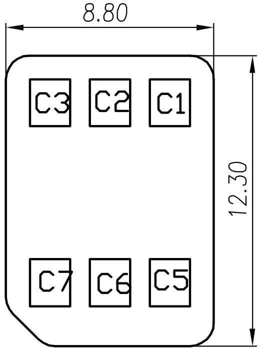
STEP 1 INSERT Micro-SIM CARD

STEP 2 PUSH THE SHELL

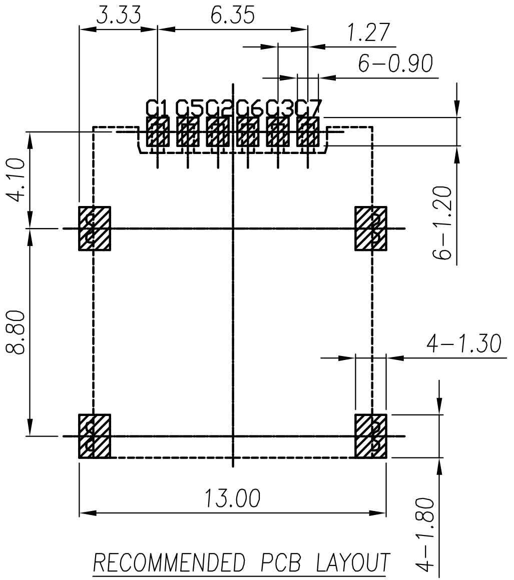
STEP 3 FINISH

*Electrical Characteristics:
Contact Current Rating:0.5 Amperes.
Dielectric Withstanding Voltage:AC500V r.m.s.
Insulation Resistance:1000 MΩ Minimum.
Contact Resistance:100 mΩ Maximum.
*Environmental:
Operating Temperature:−25°C~+90°C.
*Environmental:
Mating Cyeles:5000~10,000 Insertions.
*Mechanical Characteristics:
Card Push Insertion/Out Force:1.4kgf. MAX
Contact Separation Force:0.20kgf Minimum.
*Material:
Insulator:HI-Temp Plastic UL 94V-0 Rated.
Contact:Copper Alloy(t=0.15mm).
Shell:Stainless Steel(t=0.20mm).
Spring:SWP.

SD5211-140-G68
G:半金G/Fu" — 6:LCP黑色



NANO SIM CARD



RECOMMENDED PCB LAYOUT
GENERAY TOLERANCE ±0.05

SIM CARD	
Pin No.	NAME
C1	VCC
C2	RST
C3	CLK
C5	GND
C6	VPP
C7	I/O

TOLERANCE UNLESS OTHERWISE SPECIFIED		HLW 深圳市华联威电子科技有限公司 HUA LIAN WEI TECHNOLOGY ELECTRONICS CO;LTD.			
.XXX ±0.10 .XX ±0.20 .X ±0.30	.X° ±3° .XX° ±2°				
APPROVED		PART NAME:	NANO 1.5H SIM 掀盖式卡座6PIN卡座		
CHECKED		PART No:	SD5211-140-G68		C
DRAWED	chenyiting	PROJECTION:	UNIT:	SCALE	SHEET
DATE	2023.04.19	⊕◁	mm	1:1	1OF1

REV.: A